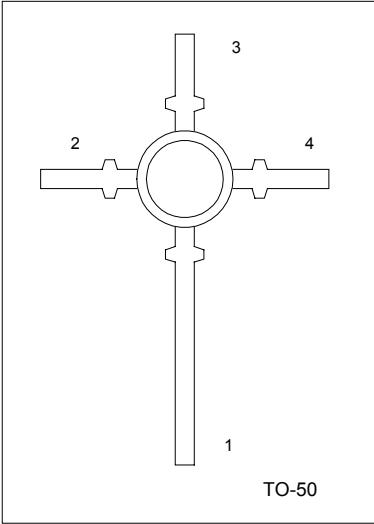


UTC 2SC3358 NPN SILICON EPITAXIAL TRANSISTOR

HIGH FREQUENCY LOW NOISE
AMPLIFIER

FEATURES

- *Low Noise and High Gain
- *High Power Gain



1:COLLECTOR 2:EMITTER 3:BASE 4:EMITTER

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	VCBO	20	V
Collector-emitter voltage	VCEO	12	V
Emitter-base voltage	VEBO	3	V
Collector current	Ic	100	mA
Total power dissipation	PT	250	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-65 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cutoff Current	ICBO	VCB=10V, IE=0			1.0	μA
Emitter Cutoff Current	IEBO	VEB=1V, IC=0			1.0	μA
DC Current Gain	hFE	VCE=10V, IC=20mA	50		300	
Gain bandwidth Product	fT	VCE=10V, IC=20mA		7		GHz
Feed-Back Capacitance	Cre	VCB=10V, IE=0, f=1.0MHz			1.0	pF
Noise figure	NF	VCE=10V, IC=7mA, f=1.0GHz			2.0	dB

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